

DEVICES AND IC's
Session D&IC: Poster presentations

Chair:

- A. Manolescu**, “Politehnica” University of
Bucharest, Romania
C. Stanescu, ON Semiconductor Romania S.R.L.,
Bucharest, Romania

D&IC.1 *ASPECTS CONCERNING CYCLE-TO-CYCLE JITTER IN A COMPARATOR BASED RELAXATION OSCILLATOR*, **M. Mocanu**¹, **M. Gurzun**¹, **L. Goras**^{1,2}, ¹“Gheorghe Asachi” Technical Univ., ²Inst. of Computer Science, Iasi, Romania.

D&IC.2 *UNCONVENTIONAL TRANSISTOR SIZING FOR REDUCING POWER ALLEVIATES THRESHOLD VOLTAGE VARIATIONS*, **A. Beg**, **V. Beiu**, **W. Ibrahim**, United Arab Emirates Univ., Abu Dhabi, United Arab Emirates.

D&IC.3 *LOW POWER AND HIGHLY RELIABLE GATES USING ARRAYS OF OPTIMALLY SIZED TRANSISTORS*, **V. Beiu**, **L. Iordaconiu***, **A. Beg**, **W. Ibrahim**, **F. Kharbash**, United Arab Emirates Univ., Abu Dhabi, United Arab Emirates, *Univ. “Politehnica” of Timisoara, Romania.

D&IC.4 *AN ACTIVE SWITCH IMPROVED DICKSON CHARGE PUMP IMPLEMENTED IN A BCD PROCESS*, **A. Joita**¹, **V. Matei**², **O. Profirescu**^{4,5}, **S. Nedelcu**³, **M. Bodea**⁴, **M. Profirescu**⁴, ¹ROHM Semiconductor European Design Centre, Willich, Germany, ²ON Semiconductor Oudenaarde, Belgium, ³Infineon Technologies Romania, Bucharest, ⁴Univ. “Politehnica” of Bucharest, ⁵ON Semiconductor Romania SRL, Bucharest, Romania.

- D&IC.5** *EXTINCTION SPECTRA AND NEAR-FIELD ENHANCEMENT OF METALLIC NANOPARTICLES*, **T. Sandu, G. Boldeiu**, IMT Bucharest, Romania.
- D&IC.6** *A SIMPLE METHOD FOR POWER LOSS ESTIMATION IN PWM INVERTER-FED MOTORS*, **S.G. Rosu, C. Radoi, M. Teodorescu, P. Guglielmi*, I.R. Bojoi*, M. Pastorelli***, “Politehnica” Univ. of Bucharest, Romania, *Politecnico di Torino, Italy.
- D&IC.7** *HIGH TEMPERATURE CHARACTERIZATION SYSTEM FOR SILICON CARBIDE DEVICES*, **L. Teodorescu¹, F. Draghici^{1,2}, G. Brezeanu¹, I. Rusu¹**, ¹“Politehnica” Univ. of Bucharest, ²IMT Bucharest, Romania.
- D&IC.8** *SIMULATIONS OF THE NOTHING ON INSULATOR NANO-TRANSISTOR IMPLEMENTED IN n-TYPE DIAMOND*, **C. Ravariu**, Univ. “Politehnica” of Bucharest, Romania.
- D&IC.9** *THE EFFECT OF THE POST-METALLIZATION ANNEALING OF Ni/n-TYPE 4H-SiC SCHOTTKY CONTACT*, **R. Pascu¹, F. Craciunoiu¹, M. Kusko¹, F. Draghici^{2,1}, A. Dinescu¹, M. Danila¹**, ¹IMT Bucharest, ²Univ. “Politehnica” of Bucharest, Romania.

20:30 BANQUET, RINA Sinaia Hotel, Restaurant Hall
